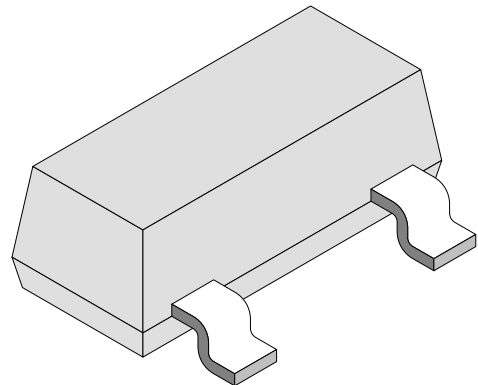




350 mW Surface Mount Zener Diodes

Features

- Planar die construction
- 350 mW Power dissipation
- Zener voltages from 2.7V – 51V
- Ideally suited for automated assembly processes



94 8550

Absolute Maximum Ratings

$T_j = 25^\circ\text{C}$

| Parameter | Test Conditions | Symbol | Value | Unit |
|--|--|-----------------|------------|------------------|
| Power dissipation | on ceramic substrate 10mm x 8mm x 0.7mm | P_d | 350 | mW |
| Zener current (see figures 1–3 below) | | | | |
| Junction and storage temperature range | | $T_j = T_{stg}$ | -55...+150 | $^\circ\text{C}$ |

Maximum Thermal Resistance

$T_j = 25^\circ\text{C}$

| Parameter | Test Conditions | Symbol | Value | Unit |
|------------------|---|------------|-------|------|
| Junction ambient | on ceramic substrate 10mm x 8mm x 0.7mm | R_{thJA} | 420 | K/W |

Electrical Characteristics

$T_j = 25^\circ\text{C}$

| Parameter | Test Conditions | Type | Symbol | Min | Typ | Max | Unit |
|-----------------|----------------------|------|--------|-----|-----|-----|------|
| Forward Voltage | $I_F = 10\text{ mA}$ | | V_F | | | 0.9 | V |

BZX84C2V7–BZX84C51



查询"BZX84C33-7.5"供应商
Vishay Telefunken

| Type | Marking | V _Z | Z _{ZT} | @ I _{ZT} | Z _{ZK} | @ I _{ZK} | T _C | I _R | @ V _R |
|-----------|---------|-------------------|-----------------|-------------------|-----------------|-------------------|----------------|----------------|----------------------|
| BZX84C... | | V | Ω | mA | Ω | mA | %/°C | μA | V |
| | | @ I _{ZT} | | | | | | | |
| 2V7 | KZC | 2.5 to 2.9 | 100 | 5.0 | 600 | 1.0 | -0.065 | 20 | 1.0 |
| 3V0 | KZD | 2.8 to 3.2 | 100 | 5.0 | 600 | 1.0 | -0.060 | 10 | 1.0 |
| 3V3 | KZE | 3.1 to 3.5 | 95 | 5.0 | 600 | 1.0 | -0.055 | 5.0 | 1.0 |
| 3V6 | KZF | 3.4 to 3.8 | 95 | 5.0 | 600 | 1.0 | -0.055 | 5.0 | 1.0 |
| 3V9 | KZG | 3.7 to 4.1 | 90 | 5.0 | 600 | 1.0 | -0.050 | 3.0 | 1.0 |
| 4V3 | KZH | 4.0 to 4.6 | 90 | 5.0 | 600 | 1.0 | -0.035 | 3.0 | 1.0 |
| 4V7 | KZ1 | 4.4 to 5.0 | 80 | 5.0 | 500 | 1.0 | -0.015 | 4.0 | 2.0 |
| 5V1 | KZ2 | 4.8 to 5.4 | 60 | 5.0 | 480 | 1.0 | +0.005 | 2.0 | 2.0 |
| 5V6 | KZ3 | 5.2 to 6.0 | 40 | 5.0 | 400 | 1.0 | +0.020 | 1.0 | 2.0 |
| 6V2 | KZ4 | 5.8 to 6.6 | 10 | 5.0 | 150 | 1.0 | +0.030 | 3.0 | 4.0 |
| 6V8 | KZ5 | 6.4 to 7.2 | 15 | 5.0 | 80 | 1.0 | +0.045 | 2.0 | 4.0 |
| 7V5 | KZ6 | 7.0 to 7.9 | 15 | 5.0 | 80 | 1.0 | +0.050 | 1.0 | 5.0 |
| 8V2 | KZ7 | 7.7 to 8.7 | 15 | 5.0 | 80 | 1.0 | +0.055 | 0.7 | 5.0 |
| 9V1 | KZ8 | 8.5 to 9.6 | 15 | 5.0 | 100 | 1.0 | +0.065 | 0.5 | 6.0 |
| 10 | KZ9 | 9.4 to 10.6 | 20 | 5.0 | 150 | 1.0 | +0.065 | 0.2 | 7.0 |
| 11 | KY1 | 10.4 to 11.6 | 20 | 5.0 | 150 | 1.0 | +0.070 | 0.1 | 8.0 |
| 12 | KY2 | 11.4 to 12.7 | 25 | 5.0 | 150 | 1.0 | +0.075 | 0.1 | 8.0 |
| 13 | KY3 | 12.4 to 14.1 | 30 | 5.0 | 170 | 1.0 | +0.080 | 0.1 | 8.0 |
| 15 | KY4 | 13.8 to 15.6 | 30 | 5.0 | 200 | 1.0 | +0.080 | 0.05 | 0.7V _{Znom} |
| 16 | KY5 | 15.3 to 17.1 | 40 | 5.0 | 200 | 1.0 | +0.090 | 0.05 | 0.7V _{Znom} |
| 18 | KY6 | 16.8 to 19.1 | 45 | 5.0 | 225 | 1.0 | +0.090 | 0.05 | 0.7V _{Znom} |
| 20 | KY7 | 18.8 to 21.2 | 55 | 5.0 | 225 | 1.0 | +0.090 | 0.05 | 0.7V _{Znom} |
| 22 | KY8 | 20.8 to 23.3 | 55 | 5.0 | 250 | 1.0 | +0.090 | 0.05 | 0.7V _{Znom} |
| 24 | KY9 | 22.8 to 25.6 | 70 | 5.0 | 250 | 1.0 | +0.090 | 0.05 | 0.7V _{Znom} |
| 27 | KYA | 25.1 to 28.9 | 80 | 2.0 | 300 | 0.5 | +0.090 | 0.05 | 0.7V _{Znom} |
| 30 | KYB | 28 to 32 | 80 | 2.0 | 300 | 0.5 | +0.090 | 0.05 | 0.7V _{Znom} |
| 33 | KYC | 31 to 35 | 80 | 2.0 | 325 | 0.5 | +0.090 | 0.05 | 0.7V _{Znom} |
| 36 | KYD | 34 to 38 | 90 | 2.0 | 350 | 0.5 | +0.090 | 0.05 | 0.7V _{Znom} |
| 39 | KYE | 37 to 41 | 130 | 2.0 | 350 | 0.5 | +0.110 | 0.05 | 0.7V _{Znom} |
| 43 | KYF | 40 to 46 | 150 | 2.0 | 375 | 0.5 | +0.110 | 0.05 | 0.7V _{Znom} |
| 47 | KYG | 44 to 50 | 170 | 2.0 | 375 | 0.5 | +0.110 | 0.05 | 0.7V _{Znom} |
| 51 | KYH | 48 to 54 | 180 | 2.0 | 400 | 0.5 | +0.110 | 0.05 | 0.7V _{Znom} |

1) Device mounted on ceramic substrate 8mmx10mmx0.7mm

2) V_Z measured at I_{ZT} using a pulse test. I_Z pulse width = 5 ms. Standard voltage tolerance is 5%.



Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise specified)

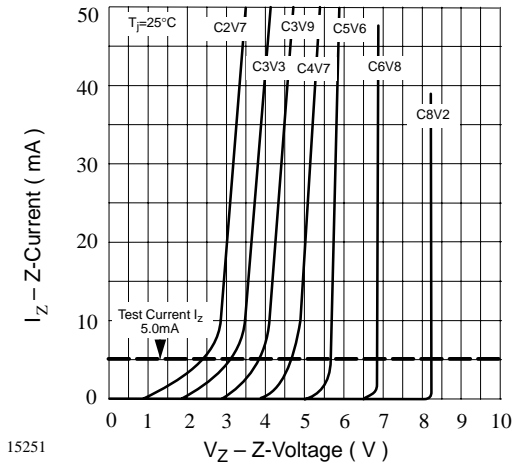


Figure 1. Z-Current vs. Z-Voltage

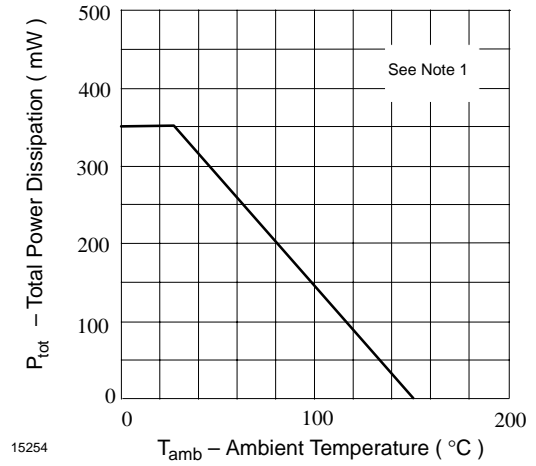


Figure 4. Total Power Dissipation vs. Ambient Temperature

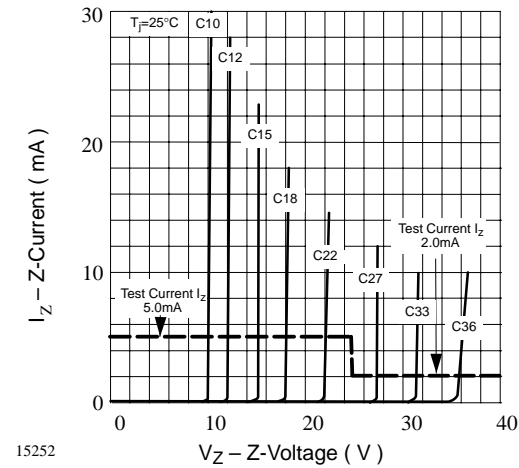


Figure 2. Z-Current vs. Z-Voltage

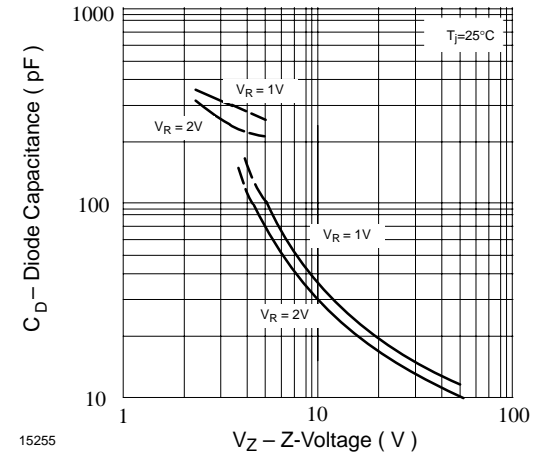


Figure 5. Diode Capacitance vs. Z-Voltage

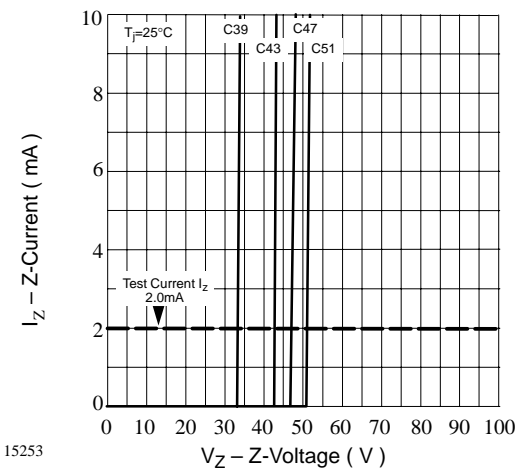


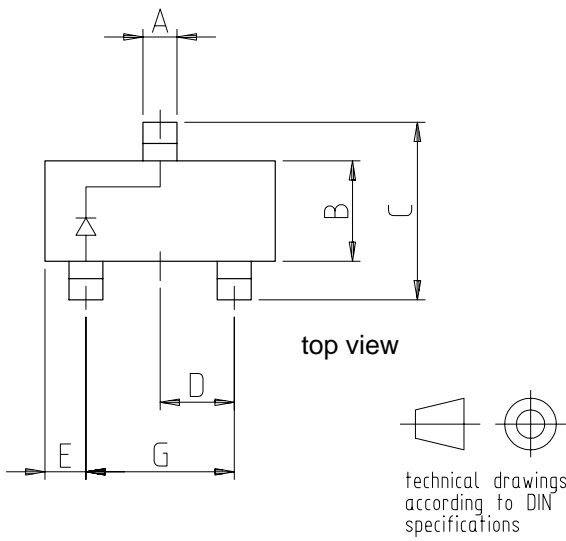
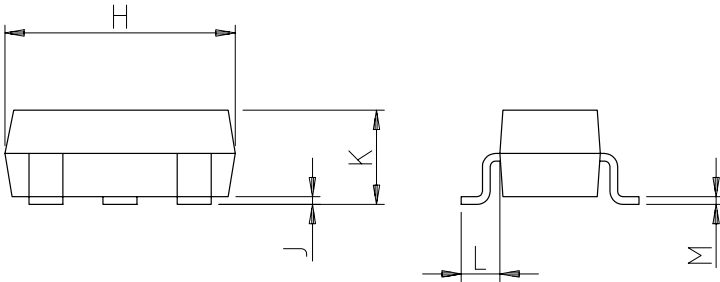
Figure 3. Z-Current vs. Z-Voltage

BZX84C2V7-BZX84C51



查询"BZX84C2V7-BZX84C51"供应商
 Vishay Telefunken

Dimensions in mm



| SOT-23 | | |
|----------------------|-------|-------|
| Dim | Min | Max |
| A | 0.37 | 0.50 |
| B | 1.19 | 1.40 |
| C | 2.10 | 2.50 |
| D | 0.89 | 1.05 |
| E | 0.45 | 0.61 |
| G | 1.78 | 2.05 |
| H | 2.79 | 3.05 |
| J | 0.013 | 0.15 |
| K | 0.89 | 1.10 |
| L | 0.45 | 0.61 |
| M | 0.076 | 0.130 |
| All Dimensions in mm | | |

14370

Case: SOT23, molded plastic
 Mounting position: any
 Approx. weight: 0.008 grams



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems
with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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